







## **Features**

- Glass passivated junction chip
- ♦ For surface mounted application
- ♦ Low profile package
- ♦ Built-in strain rellef
- ♦ Ideal for automated placement
- ♦ Easy pick and place
- ♦ Super fast recovery time for high efficiency
- ♦ Qualified as per AEC-Q101
- → High temperature soldering: 260°C/10 seconds at terminals
- Plastic material used carries Underwriters Laboratory Classification 94V-0
- Green compound with suffix "G" on packing code & prefix "G" on datecode

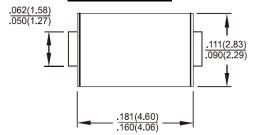
### **Mechanical Data**

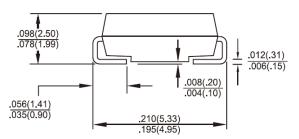
- ♦ Case: Molded plastic
- → Terminals: Pure tin plated, lead free
- Polarity: Indicated by cathode band
- ♦ Packing: 12mm tape per EIA STD RS-481
- ♦ Weight: 0.067 grams

# ESH2BA - ESH2DA

1.0AMPS Surface Mount Super Fast Rectifiers

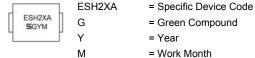
## SMA/DO-214AC





# **Dimensions in inches and (millimeters)**

#### **Marking Diagram**



# **Maximum Ratings and Electrical Characteristics**

Rating at 25  $^{\circ}$ C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Type Number	Symbol	ESH2BA	ESH2CA	ESH2DA	Unit
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	100	150	200	V
Maximum RMS Voltage	$V_{RMS}$	70	105	140	V
Maximum DC Blocking Voltage	$V_{DC}$	100	150	200	V
Maximum Average Forward Rectified Current	I <sub>F(AV)</sub>	1			Α
Peak Forward Surge Current, 8.3 ms Single Half Sinewave Superimposed on Rated Load	I <sub>FSM</sub>	50			А
Maximum Instantaneous Forward Voltage (Note 1) @ 1 A	V <sub>F</sub>	0.90			V
Maximum Reverse Current @ Rated VR $T_A$ =25 $^{\circ}$ C $T_A$ =125 $^{\circ}$ C	I <sub>R</sub>	1 50			uA
Maximum Reverse Recovery Time (Note 2)	Trr	25			nS
Typical Junction Capacitance (Note 3)	Cj	25			pF
Typical Thermal Resistance	$R_{ heta jA} \ R_{ heta jL}$	75 20			°C/W
Operating Temperature Range	$T_J$	- 55 to + 175			οС
Storage Temperature Range	T <sub>STG</sub>	- 55 to + 175			°С

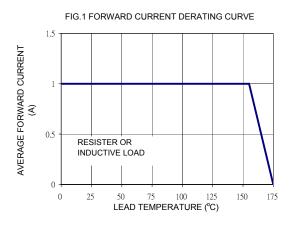
Note 1: Pulse Test with PW=300 usec, 1% Duty Cycle

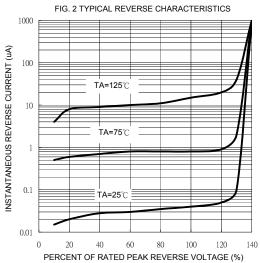
Note 2: Reverse Recovery Test Conditions: I<sub>F</sub>=0.5A, I<sub>R</sub>=1.0A, I<sub>RR</sub>=0.25A

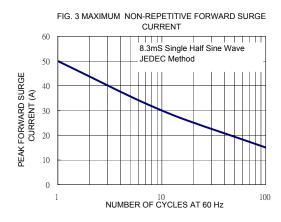
Note 3: Measured at 1 MHz and Applied Reverse Voltage of 4.0V D.C.

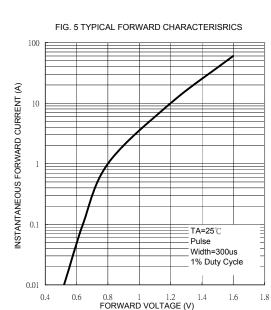


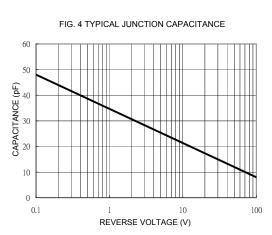
## RATINGS AND CHARACTERISTIC CURVES (ESH2BA THRU ESH2DA)











## FIG.6- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM

